

SANYO	No. 1594B	2SC3460
NPN Triple Diffused Planar Silicon Transistor		
FOR SWITCHING REGULATORS		

Features

- . High breakdown voltage and high reliability.
- . Fast switching speed (t_f : 0.1 μ s typ.)
- . Wide ASO.
- . Adoption of MBIT process.

Absolute Maximum Ratings at Ta=25°C

			unit
Collector-to-Base Voltage	V _{CB0}	1100	V
Collector-to-Emitter Voltage	V _{CE0}	800	V
Emitter-to-Base Voltage	V _{EBO}	7	V
Collector Current	I _C	6	A
Peak Collector Current	i _{cp}	20	A
Base Current	I _B	3	A
Collector Dissipation	P _C	100	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

$T_C=25^\circ\text{C}$
PW \leq 300 μ s, Duty Cycle \leq 10%

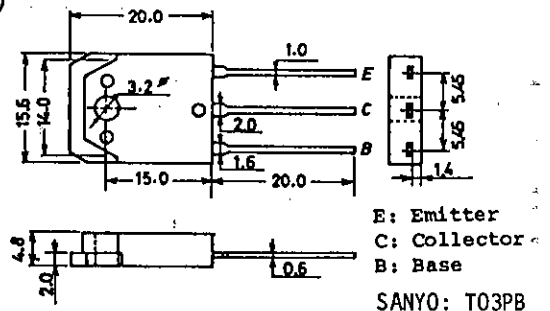
Electrical Characteristics at Ta=25°C

		min	typ	max	unit	
Collector Cutoff Current	I _{CB0}			10	μ A	
Emitter Cutoff Current	I _{EBO}			10	μ A	
DC Current Gain	h _{FE(1)}	10*		40*		
	h _{FE(2)}	8				
Gain-Bandwidth Product	f _T		15		MHz	
Output Capacitance	c _{ob}		120		pF	
C-E Saturation Voltage	V _{CE(sat)}			2.0	V	
B-E Saturation Voltage	V _{BE(sat)}			1.5	V	
C-B Breakdown Voltage	V(BR)CBO	1100			V	
C-E Breakdown Voltage	V(BR)CEO	800			V	
E-B Breakdown Voltage	V(BR)EBO	7			V	
C-E Sustain Voltage	V _{CEX(sus)}	800			V	
Turn-On Time	t _{on}	$V_{CC}=400\text{V},$ $5I_{B2}=-2.5I_{B2}=I_C=4\text{A},$ $R_L=100\text{ohms}$			0.5	μ s
Storage Time	t _{stg}				3.0	μ s
Fall Time	t _f				0.3	μ s

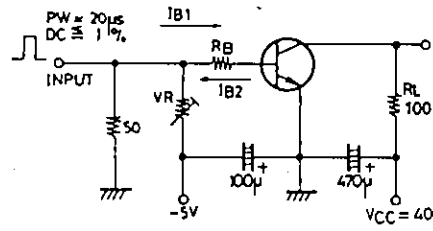
*: The h_{FE(1)} of the 2SC3460 is classified as follows. When specifying the h_{FE(1)} rank, specify two ranks or more in principle.

10	K	20	15	L	30	20	M	40
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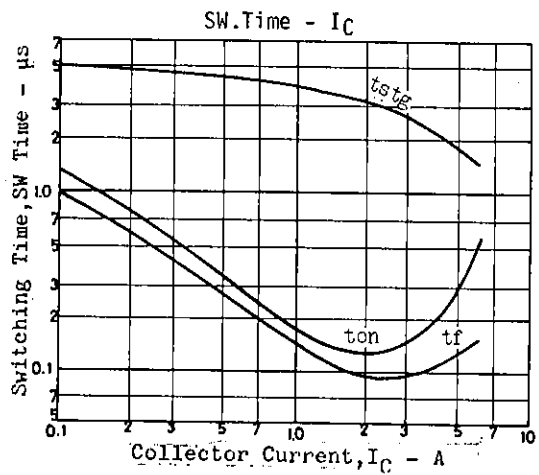
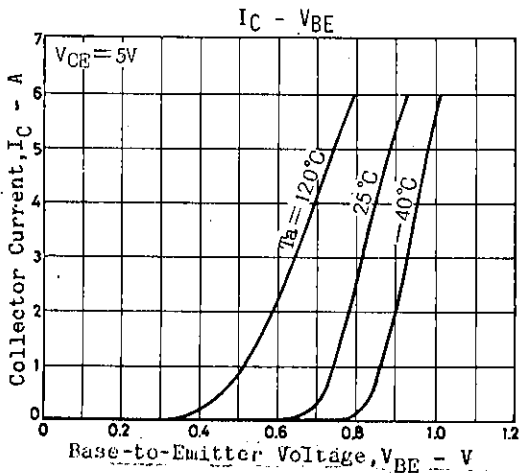
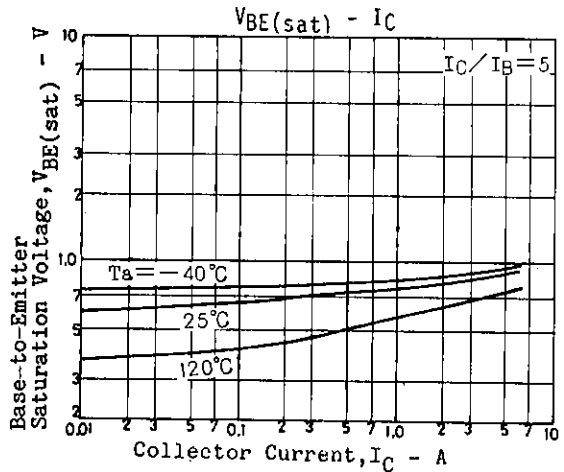
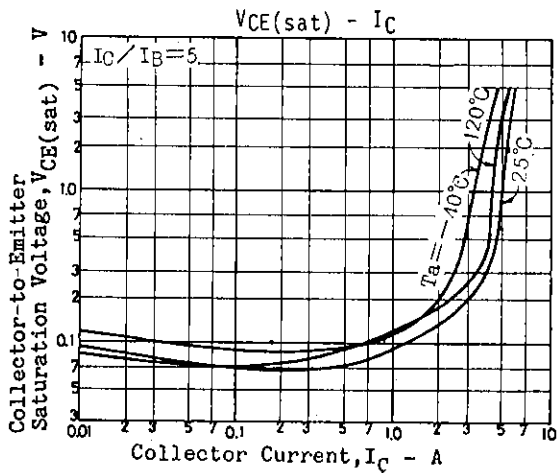
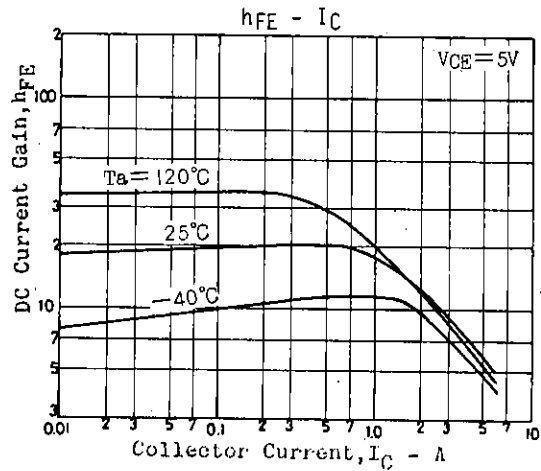
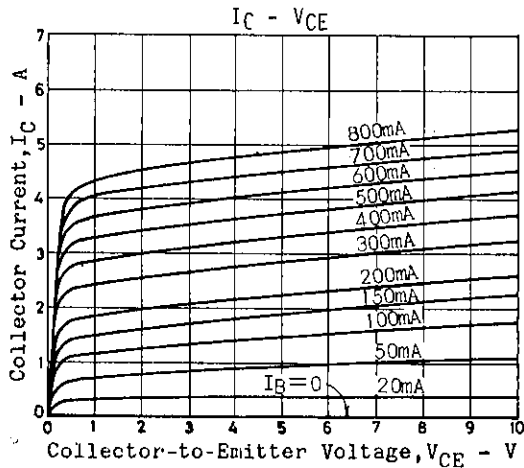
Package Dimensions 2022
(unit:mm)

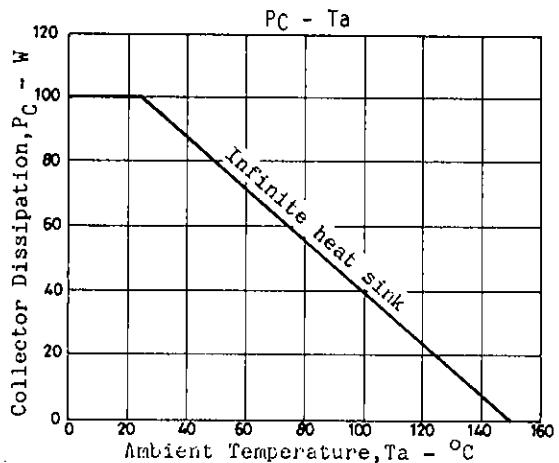
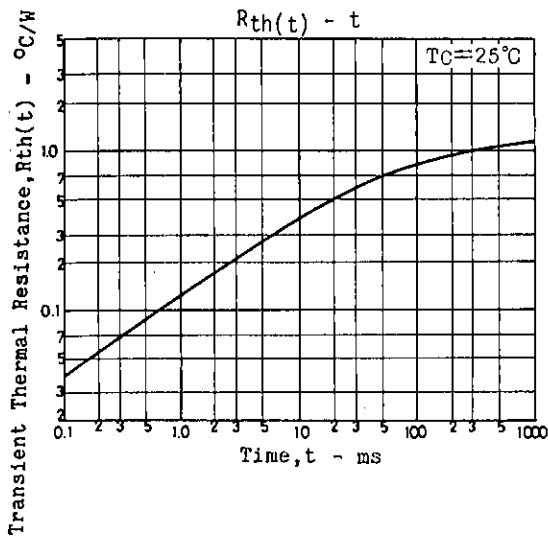
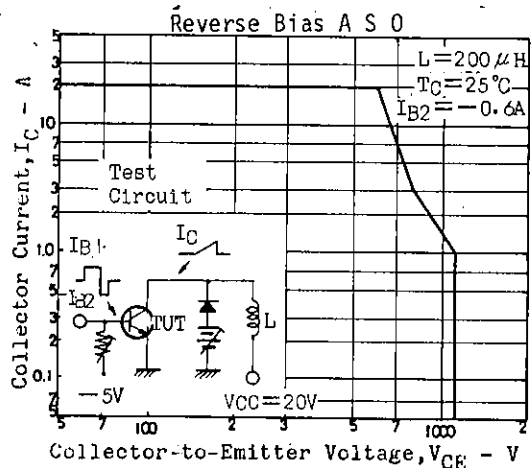
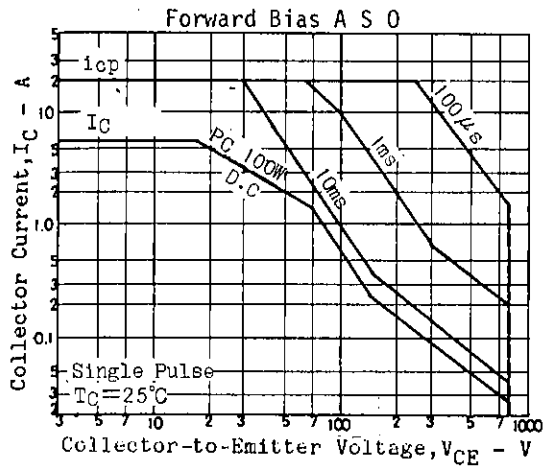


Switching Time Test Circuit



Unit (Resistance : Ω, Capacitance : F)





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